AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A method for the fabrication of a semiconductor light-emitting device, comprising the steps of:

stacking at least a first conductive type semiconductor layer, an active layer and a second conductive type semiconductor layer on a substrate to form a wafer;

forming on a side of growth surfaces of the semiconductor layers first trenches ~~exposing~~ so as to expose a lateral surface of the first conductive type semiconductor layer at the end of the first trench forming step;

forming second trenches reaching the substrate from above the first trenches by the use of a laser beam so that at least a part of the lateral surface of the first conductive type semiconductor layer remains exposed at the end of the second trench forming step;

forming third trenches from the substrate at positions corresponding to the second trenches by the use of a laser beam;

using a dicing blade to correct a shape of the third trenches; and

dividing the wafer into chips.

2. (original): A method according to claim 1, wherein the third trenches have a greater width than the second trenches.

3. (previously presented): A method according to claim 1, wherein the third trenches have a greater width than the first trenches.

4. (canceled).

5. (canceled).

6. (previously presented): A method according to claim 1, wherein the third trenches are formed by radiating a laser beam two times or more.

7. (previously presented): A method according to claim 1, wherein the substrate is lapped, ground or polished till a thickness thereof reaches 100 μm or less inclusive of an epitaxial layer prior to the formation of the third trenches.

8. (previously presented): A method according to claim 1, wherein the first conductive type semiconductor layer is an n-type semiconductor layer and the second conductive type semiconductor layer is a p-type semiconductor layer.

9. (previously presented): A method according to claim 1, wherein the substrate is a sapphire substrate.

10. (previously presented): A method according to claim 1, wherein the semiconductor light-emitting device is a nitride-based semiconductor light-emitting device.

11. (previously presented): A method according to claim 1, wherein the semiconductor light-emitting device is a gallium nitride-based semiconductor light-emitting device.

12. (previously presented): A semiconductor light-emitting device produced by using the method for the fabrication of the semiconductor light-emitting device according to claim 1.